an insulating substrate;

an active matrix circuit including at least one thin film transistor formed over a first surface of said insulating substrate;

<u>a</u> driving [means] <u>circuit</u> including at least another one thin film transistor for driving the active matrix circuit <u>formed over said first surface of the insulating substrate</u>; [and]

a counter substrate facing the first surface of said insulating substrate with a liquid crystal material disposed therebetween, wherein said insulating substrate extends beyond at least one side edge of the counter substrate so as to provide an extended portion; and

at least one semiconductor integrated circuit chip [for controlling] <u>disposed</u> over said first surface of the extended portion of the insulating substrate and operationally <u>connected with</u> the driving means,

wherein [the active matrix circuit, the driving means and the semiconductor integrated circuit chip are formed on] said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over the first surface of the insulating substrate.

- To
- 2. (Amended) The device of claim 1 wherein the semiconductor integrated circuit chip is connected with the driving [means] <u>circuit</u> by a wire bonding.
- 3. (Amended) The device of claim 1 wherein the semiconductor integrated circuit chip is connected with the driving [means] <u>circuit</u> by a COG (chip on glass).
- 6. (Amended) The device of claim 1 wherein the <u>insulating</u> substrate comprises a glass substrate.



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7. (Twice Amended) A liquid crystal display device comprising:

a substrate [comprising a glass substrate] having a first surface;

an active matrix circuit including at least one thin film transistor <u>formed</u> over the first surface of the substrate;

<u>a</u> driving [means] <u>circuit</u> including at least another one thin film transistor for driving the active matrix circuit <u>formed over the first surface of the substrate</u>; and

[control means including at least another one thin film transistor for driving

the active matrix circuit; and]

[control means for controlling the driving means, the control means has] at least one semiconductor integrated circuit chip disposed over the first surface of the substrate and operationally connected to said driving circuit.

wherein [the active matrix circuit, the driving means and the control means are formed on the substrate] said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over the first surface of the substrate, and wherein said at least one thin film transistor of the active matrix circuit has at least one lightly doped drain between a channel region and a drain region thereof.

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13 (Thrice Amended) A liquid crystal display device comprising:

an insulating substrate;

an active matrix circuit including at least one thin film transistor;

a driving [means] <u>circuit</u> including at least another one thin film transistor for driving the active matrix circuit; and

a control [means] <u>circuit</u> for controlling the driving [means] <u>circuit</u>, the control [means] <u>circuit</u> being <u>operationally</u> connected with the driving [means by a COG (chip on glass)] <u>circuit</u>,

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wherein the active matrix circuit, driving [means] <u>circuit</u> and the control [means] <u>circuit</u> are formed on the insulating substrate and wherein the control means has at least one semiconductor integrated <u>circuit</u> chip, <u>and</u>

wherein said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over said insulating substrate.

16. (Thrice Amended) A liquid crystal display device comprising:

an insulating substrate;

an active matrix circuit including at least one thin film transistor;

a driving [means] <u>circuit</u> including at least another one thin film transistor for driving the active matrix circuit; and

[control means for controlling the driving means, the control means being connected with the driving means by a wire bonding,]

a semiconductor integrated circuit chip mounted over said insulating substrate and operationally connected to said driving circuit.

wherein the active matrix circuit[,] and the driving [means and the control means] circuit are formed from a common semiconductor film formed over [on] the insulating substrate [and wherein the control means has at least one semiconductor integrated circuit chip].

(Twice Amended) An electric device comprising:

a substrate having an insulating surface;

a plurality of thin film transistors formed on the insulating surface, said plurality of thin film transistors being formed from a common semiconductor film formed on said insulating surface; and

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at least one single crystalline semiconductor integrated circuit chip formed on the insulating surface;

wherein at least one of the thin film transistors is provided as an active matrix circuit, at least another one of the thin film transistors is provided as at least one driving circuit for driving the active matrix circuit and the semiconductor integrated circuit chip is provided as a control circuit for controlling the driving circuit, and wherein said common semiconductor film is formed by crystallizing a semiconductor film comprising amorphus silicon deposited on said insulating surface.

21. (Twice Amended) An electric device comprising:

a [pair of insulating substrates opposite to each other] <u>first substrate</u>; an active matrix circuit formed [by] <u>over said first substrate with</u> at least one thin film transistor;

a driving circuit formed by over said first substrate with at least one other thin film transistor for driving the active matrix circuit; [and]

a second substrate facing said first substrate with a gap therebetween, said first substrate extending beyond at least one side edge of the second substrate to provide an extended portion; and

a [single crystalline] semiconductor integrated circuit chip <u>disposed over the</u> extended portion of said first substrate and operationally connected to said driving circuit,

wherein [the active matrix circuit, the driving circuit and the single crystalline semiconductor integrated circuit are formed on one of the insulating substrate, and

wherein the driving circuit has at least an X-decoder/driver and a Y-decoder/driver] said at least one thin film transistor and said one other thin film transistor are formed from a common semiconductor film obtained by crystallizing a semiconductor film comprising amorphous silicon deposited over said first substrate.

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Please add new claims 32-35 as follows:

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32. A liquid crystal display device comprising:

a first substrate having an insulating surface;

an active matrix circuit including a first plurality of thin film transistors formed on the insulating surface of the first substrate;

a driving circuit including a second plurality of thin film transistors formed over the insulating surface of the first substrate for driving said active matrix circuit;

a second substrate facing said first substrate with a liquid crystal material interposed therebetween, said first substrate having an extended portion which extends beyond at least one side edge of the second substrate;

at least one semiconductor integrated circuit chip disposed over the extended portion of the first substrate and operationally connected to said driving circuit,

wherein said first and second plurality of thin film transistors are formed from a common semiconductor film formed over said first substrate, and each of said first plurality of thin film transistors has at least one lightly doped drain between a channel region and a drain region thereof.

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A liquid crystal display device according to claim 32 wherein said semiconductor film comprises crystalline silicon.

34. A liquid crystal display device according to claim 32 wherein said semiconductor integrated circuit chip is a memory.

35. A liquid crystal display device according to claim 32 wherein said semiconductor integrated circuit chip is a CPU.--

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